



SHENZHEN TUOFENG SEMICONDUCTOR TECHNOLOGY CO.,LTD

SOT-23 Plastic-Encapsulate MOSFETs

2SK3018**2SK3018** N-Channel 30-V(D-S) MOSFET

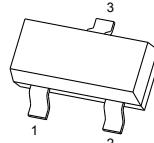
V_{(BR)DSS}	R_{D(on)MAX}	I_D
30V	2.5Ω@4.5V	0.1A
	3.0Ω@2.5V	

●Features

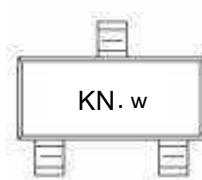
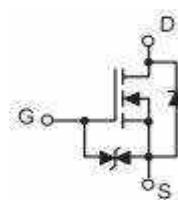
- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Low voltage drive (2.5V) makes this device ideal for portable equipment.
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.
- 6) ESD protected 2KV HBM

●Applications

Interfacing, switching (30V, 100mA)

SOT-23 SOT-323

- 1.GATE
- 2.SOURCE
- 3.DRAIN

MARKING**Equivalent Circuit**

*w: week code

Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Drain-source voltage	V _{DSS}	30	V
Gate-source voltage	V _{GSS}	±20	V
Drain current	Continuous I _D	±100	mA
	Pulsed I _{DP} * ¹	±400	mA
Total power dissipation	P _D * ²	200	mW
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

*1 P_w≤10μs, Duty cycle≤1%

*2 With each pin mounted on the recommended lands.

Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	R _{th(ch-a)} *	625	°C / W

*With each pin mounted on the recommended lands.